

Notice of References Cited

Application No.

09-700,785

Applicant(s)

Ito et. al.

Examiner

George Gouldreau

Group Art Unit

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*	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS
A	6,133,153	10-17-00	Marques et. al.	438	706
B	6,184,150	2-6-01	Yang et. al.	438	740
C					
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*	DOCUMENT NO.	DATE	COUNTRY	NAME	CLASS	SUBCLASS
N						
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S						
T						

NON-PATENT DOCUMENTS

*	DOCUMENT (Including Author, Title, Source, and Pertinent Pages)	DATE
U	"Highly Selective SiO ₂ Etch Employing Industrially Coupled Hydro-Fluorocarbon Plasma Chemistry For Self Aligned Contact Etch"; Iijima et. al.; Japanese Journal of Applied Physics; Part II; Vol. 36; 9A; pp 5498-5501; (9-1997)	
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* A copy of this reference is not being furnished with this Office action.
(See Manual of Patent Examining Procedure, Section 707.05(a).)